

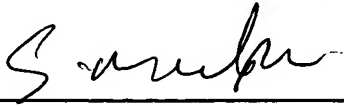
INFORMATION DISCLOSURE STATEMENT	Atty Docket: Serial No.: Applicant: Filing Date: Group:	62603_CON1 NOT YET ASSIGNED MEARS HEREWITH	10/716,783

U.S. PATENT DOCUMENTS								
Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date	
SM	AA	4,594,603	06/10/86	Holonyak, Jr.	357	16	01/24/85	
	AB	4,937,204	06/26/90	Ishibashi et al.	437	110	01/4/89	
[Handwritten line]	AC	4,969,031	11/06/90	Kobayashi et al.	357	63	02/3/83	
	AD	5,05,887	10/08/91	Yamazaki	357	4	01/18/90	
	AE	5,216,262	06/1/93	Tsu	257	17	03/2/92	
	AF	5,357,119	10/18/94	Wang et al.	257	18	02/19/93	
	AG	5,684,817	11/04/97	Houdre et al.	372	45	05/1/96	
	AH	5,683,934	11/4/03	Candelaria	437	134	05/3/96	
	AI	5,994,164	11/30/99	Fonash et al.	438	97	03/18/98	
	AJ	6,058,127	05/2/00	Joannopoulos et al.	372	92	12/12/97	
	AK	6,274,007	08/14/01	Smirnov et al.	204	192	03/14/00	
	AL	6,281,518	08/28/01	Sato	257	13	12/3/98	
	AM	6,281,532	08/28/01	Doyle et al.	257	288	06/28/99	
	AN	6,344,271	02/05/02	Yadav et al.	428	402	03/23/99	
	AO	6,472,685	10/29/02	Takagi	257	77	12/2/98	
	AP	6,498,359	12/24/02	Schmidt et al.	257	190	05/18/01	
	AQ	2003/ 0034529	02/20/03	Fitzgerald et al.	257	369	10/8/02	
	BS	AR	2003/ 0057416	03/27/03	Currie et al.	257	19	09/20/02
	FOREIGN PATENT DOCUMENTS							
			Document Number	Date	Country	Class	Sub Class	Translation
SM SM	AS	02/103767	12/27/02	WO	H01L	21/20		
	AT	2,347,520	09/06/00	GB	G02B	5/18		
	AU							

EXAMINER: <i>G. [Signature]</i>	DATE CONSIDERED: <i>7/24/04</i>
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>	

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	Applicant: Filing Date: Group:	NOT YET ASSIGNED MEARS HEREWITH

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
Sm	AV	Xuan Luo et al.; "Chemical Design of Direct-Gap Light-Emitting Silicon", published July 25, 2002 by The American Physical Society; Vol. 89, Number 7
	AW	R. Tsu; University of North Carolina at Charlotte, "Phenomena in Silicon Nanostructure Devices"; published 09/06/2000 © Springer-Verlag 2000
	AX	P.D. Ye et al., "GaAs MOSFET with Oxide Gate Dielectric Grown by Atomic Layer Deposition"; © 2003 Agere Systems, March 2003
Sm	AY	Novikov et al.; "Silicon-based Optoelectronics" © 1999-2003 by John Wiley & Sons, Inc.; pp/ 1-6
	AZ	
	BA	

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Sheet 1 of 1

**INFORMATION DISCLOSURE
STATEMENT**

Atty Docket: 62603_CON1
Serial No.: 10/716,783
Applicant: MEARS ET AL.
Filing Date: NOVEMBER 19, 2003
Group:

U.S. PATENT DOCUMENTS

Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
gm	AA	4,485,128	11/27/84	Dalal et al.	427	85	
	AB	6,326,311	12/4/01	Ueda et al.	438	694	
	AC	6,350,993	2/26/02	Chu et al.	257	19	
	AD	6,376,337	4/23/02	Wang et al.	438	478	
	AE	6,436,784	8/20/02	Allam	438	380	
	AF	6,501,092	12/31/02	Nikonov et al.	257	29	
	AG	6,566,679	5/20/03	Nikonov et al.	257	29	
	AH	6,621,097	9/16/03	Nikonov et al.	257	17	
	AI	2003/0162335	8/28/03	Yuki et al.	438	151	3/4/03
SM	AJ	2003/0215990	11/20/03	Fitzgerald et al.	438	172	3/14/03
	AK						
	AL						
	AM						
	AN						
	AO						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Sub Class	Translation
SM	AP	61220339A	9/30/86	Japan	H01L21	322	English Abstract
SM	AQ	61145820A	7/3/86	Japan	H01L21	20	English Abstract
SM	AR	99/63580	12/9/99	WO	H01L3	00	n/a

EXAMINER:

S. Auer

DATE CONSIDERED:

7/2/04

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